

Francesco Montalenti

List of Publications by Citations

Source: <https://exaly.com/author-pdf/1367404/francesco-montalenti-publications-by-citations.pdf>

Version: 2024-04-19

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

150
papers

3,753
citations

30
h-index

56
g-index

153
ext. papers

3,991
ext. citations

4.4
avg, IF

5.14
L-index

#	Paper	IF	Citations
150	Extending the Time Scale in Atomistic Simulation of Materials. <i>Annual Review of Materials Research</i> , 2002 , 32, 321-346	12.8	543
149	Crossover among structural motifs in transition and noble-metal clusters. <i>Journal of Chemical Physics</i> , 2002 , 116, 3856-3863	3.9	383
148	Jumps and concerted moves in Cu, Ag, and Au(110) adatom self-diffusion. <i>Physical Review B</i> , 1999 , 59, 5881-5891	3.3	127
147	Atomic-scale pathway of the pyramid-to-dome transition during ge growth on Si(001). <i>Physical Review Letters</i> , 2004 , 93, 216102	7.4	104
146	Delayed Plastic Relaxation on Patterned Si Substrates: Coherent SiGe Pyramids with Dominant {111} Facets. <i>Physical Review Letters</i> , 2007 , 98,	7.4	91
145	Structure and mobility of defects formed from collision cascades in MgO. <i>Physical Review Letters</i> , 2004 , 92, 115505	7.4	90
144	Leapfrog Diffusion Mechanism for One-Dimensional Chains on Missing-Row Reconstructed Surfaces. <i>Physical Review Letters</i> , 1999 , 82, 1498-1501	7.4	88
143	Key role of the wetting layer in revealing the hidden path of Ge/Si(001) Stranski-Krastanow growth onset. <i>Physical Review B</i> , 2009 , 80,	3.3	87
142	Enhanced relaxation and intermixing in Ge islands grown on pit-patterned Si(001) substrates. <i>Physical Review Letters</i> , 2009 , 102, 025502	7.4	78
141	Monolithic growth of ultrathin Ge nanowires on Si(001). <i>Physical Review Letters</i> , 2012 , 109, 085502	7.4	73
140	Electronic and elastic contributions in the enhanced stability of Ge(105) under compressive strain. <i>Surface Science</i> , 2004 , 556, 121-128	1.8	71
139	Closing the gap between experiment and theory: crystal growth by temperature accelerated dynamics. <i>Physical Review Letters</i> , 2001 , 87, 126101	7.4	64
138	Cell cycle effects of gemcitabine. <i>International Journal of Cancer</i> , 2001 , 93, 401-8	7.5	62
137	Modeling the plastic relaxation onset in realistic SiGe islands on Si(001). <i>Physical Review B</i> , 2008 , 78,	3.3	55
136	Faceting of Equilibrium and Metastable Nanostructures: A Phase-Field Model of Surface Diffusion Tackling Realistic Shapes. <i>Crystal Growth and Design</i> , 2015 , 15, 2787-2794	3.5	54
135	Exploiting past visits or minimum-barrier knowledge to gain further boost in the temperature-accelerated dynamics method. <i>Journal of Chemical Physics</i> , 2002 , 116, 4819	3.9	53
134	Simulation of growth of Cu on Ag(001) at experimental deposition rates. <i>Physical Review B</i> , 2002 , 66,	3.3	50

133	Competing mechanisms in adatom diffusion on a channeled surface: Jumps versus metastable walks. <i>Physical Review B</i> , 1998 , 58, 3617-3620	3-3	50
132	Critical shape and size for dislocation nucleation in Si _{1-x} Ge _x islands on Si(001). <i>Physical Review Letters</i> , 2007 , 99, 235505	7-4	48
131	Unexpected dominance of vertical dislocations in high-misfit ge/si(001) films and their elimination by deep substrate patterning. <i>Advanced Materials</i> , 2013 , 25, 4408-12	24	47
130	Self-ordering of a Ge island single layer induced by Si overgrowth. <i>Physical Review Letters</i> , 2006 , 96, 106102	7-4	42
129	Normal-incidence steering effect in crystal growth: Ag/Ag(100). <i>Physical Review B</i> , 2001 , 64,	3-3	41
128	How pit facet inclination drives heteroepitaxial island positioning on patterned substrates. <i>Physical Review B</i> , 2011 , 84,	3-3	37
127	Formation of Ge nanoripples on vicinal Si (1110): from Stranski-Krastanow seeds to a perfectly faceted wetting layer. <i>Physical Review Letters</i> , 2012 , 108, 055503	7-4	37
126	Strain-induced ordering of small Ge islands in clusters at the surface of multilayered SiGe nanostructures. <i>Applied Physics Letters</i> , 2005 , 87, 261919	3-4	36
125	Anomalous smoothing preceding island formation during growth on patterned substrates. <i>Physical Review Letters</i> , 2012 , 109, 156101	7-4	34
124	Simulating cancer-cell kinetics after drug treatment: Application to cisplatin on ovarian carcinoma. <i>Physical Review E</i> , 1998 , 57, 5877-5887	2-4	34
123	Measuring the complexity of cell cycle arrest and killing of drugs: Kinetics of phase-specific effects induced by Taxol 1999 , 37, 113-124		34
122	Fully coherent growth of Ge on free-standing Si(001) nanomesas. <i>Physical Review B</i> , 2014 , 89,	3-3	30
121	Highly Mismatched, Dislocation-Free SiGe/Si Heterostructures. <i>Advanced Materials</i> , 2016 , 28, 884-8	24	30
120	Collective shape oscillations of SiGe islands on pit-patterned Si(001) substrates: a coherent-growth strategy enabled by self-regulated intermixing. <i>Physical Review Letters</i> , 2010 , 105, 166102	7-4	29
119	Intermixing in heteroepitaxial islands: fast, self-consistent calculation of the concentration profile minimizing the elastic energy. <i>New Journal of Physics</i> , 2008 , 10, 083039	2-9	29
118	Photodetection in Hybrid Single-Layer Graphene/Fully Coherent Germanium Island Nanostructures Selectively Grown on Silicon Nanotip Patterns. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 2017-26	9-5	25
117	Dimers diffusion on (110) (1 $\bar{1}$) metal surfaces. <i>Surface Science</i> , 1999 , 432, 27-36	1-8	24
116	Imaging Structure and Composition Homogeneity of 300 mm SiGe Virtual Substrates for Advanced CMOS Applications by Scanning X-ray Diffraction Microscopy. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 9031-7	9-5	23

115	Engineered Coalescence by Annealing 3D Ge Microstructures into High-Quality Suspended Layers on Si. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 19219-25	9.5	23
114	Morphological Evolution of Pit-Patterned Si(001) Substrates Driven by Surface-Energy Reduction. <i>Nanoscale Research Letters</i> , 2017 , 12, 554	5	23
113	Stability of Ge on Si (1 1 10) surfaces and the role of dimer tilting. <i>Physical Review B</i> , 2012 , 85,	3.3	22
112	Fine control of plastic and elastic relaxation in Ge/Si vertical heterostructures. <i>Journal of Applied Physics</i> , 2014 , 116, 104306	2.5	21
111	Aspect-ratio-dependent driving force for nonuniform alloying in Stranski-Krastanow islands. <i>Physical Review B</i> , 2009 , 80,	3.3	21
110	First principles study of GeBi exchange mechanisms at the Si(001) surface. <i>Applied Physics Letters</i> , 2008 , 92, 191908	3.4	21
109	Fast isotropic adatom diffusion on Ge(105) dot facets. <i>Physical Review B</i> , 2004 , 70,	3.3	20
108	Growth kinetics and morphological analysis of homoepitaxial GaAs fins by theory and experiment. <i>Physical Review Materials</i> , 2018 , 2,	3.2	20
107	Assessing the delay of plastic relaxation onset in SiGe islands grown on pit-patterned Si(001) substrates. <i>Applied Physics Letters</i> , 2011 , 99, 033106	3.4	19
106	Atomistic modeling of step formation and step bunching at the Ge(105) surface. <i>Surface Science</i> , 2005 , 591, 23-31	1.8	19
105	Spontaneous atomic shuffle in flat terraces: Ag(100). <i>Physical Review B</i> , 2002 , 66,	3.3	19
104	Self-assembled GaAs islands on Si by droplet epitaxy. <i>Applied Physics Letters</i> , 2010 , 97, 053101	3.4	18
103	Quantitative estimate of H abstraction by thermal SiH ₃ on hydrogenated Si(001)(2×1). <i>Physical Review B</i> , 2007 , 75,	3.3	18
102	Ab initio results for the adiabatic atom-surface interaction for helium and neon on a simple metal. <i>Surface Science</i> , 1996 , 364, L595-L599	1.8	18
101	Temperature-Dependent Stability of Polytypes and Stacking Faults in SiC: Reconciling Theory and Experiments. <i>Physical Review Applied</i> , 2019 , 12,	4.3	17
100	Applying Accelerated Molecular Dynamics to Crystal Growth. <i>Physica Status Solidi (B): Basic Research</i> , 2001 , 226, 21-27	1.3	17
99	Long jumps in the strong-collision model. <i>Physical Review E</i> , 2000 , 61, 6344-50	2.4	17
98	Competition Between Kinetics and Thermodynamics During the Growth of Faceted Crystal by Phase Field Modeling. <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1800518	1.3	17

97	Phase-field simulations of faceted Ge/Si-crystal arrays, merging into a suspended film. <i>Applied Surface Science</i> , 2017 , 391, 33-38	6.7	16
96	InAs/GaAs Sharply Defined Axial Heterostructures in Self-Assisted Nanowires. <i>Nano Letters</i> , 2015 , 15, 3677-83	11.5	16
95	One-dimensional Ge nanostructures on Si(001) and Si(1 1 10): Dominant role of surface energy. <i>Comptes Rendus Physique</i> , 2013 , 14, 542-552	1.4	16
94	Local uniaxial tensile strain in germanium of up to 4% induced by SiGe epitaxial nanostructures. <i>Applied Physics Letters</i> , 2015 , 107, 083101	3.4	16
93	Crystallinity and microstructure in Si films grown by plasma-enhanced chemical vapor deposition: A simple atomic-scale model validated by experiments. <i>Applied Physics Letters</i> , 2009 , 94, 051904	3.4	16
92	Accurate and analytical strain mapping at the surface of Ge/Si(0 0 1) islands by an improved flat-island approximation. <i>Surface Science</i> , 2006 , 600, 4777-4784	1.8	16
91	Vertical and lateral ordering of Ge islands grown on Si(001): theory and experiments. <i>Journal of Physics Condensed Matter</i> , 2007 , 19, 225001	1.8	16
90	Formation of strain-induced Si-rich and Ge-rich nanowires at misfit dislocations in SiGe: A model supported by photoluminescence data. <i>Applied Physics Letters</i> , 2004 , 84, 2895-2897	3.4	16
89	Stability of shuffle and glide dislocation segments with increasing misfit in Ge _{1-x} Si _x (001) epitaxial layers. <i>Applied Physics Letters</i> , 2005 , 86, 041912	3.4	16
88	Self-organized evolution of Ge/Si(001) into intersecting bundles of horizontal nanowires during annealing. <i>Applied Physics Letters</i> , 2013 , 103, 083109	3.4	15
87	Temperature-dependent evolution of the wetting layer thickness during Ge deposition on Si(001). <i>Nanotechnology</i> , 2011 , 22, 285704	3.4	15
86	Thermal-hydrogen promoted selective desorption and enhanced mobility of adsorbed radicals in silicon film growth. <i>Physical Review Letters</i> , 2008 , 100, 046105	7.4	15
85	Modeling the competition between elastic and plastic relaxation in semiconductor heteroepitaxy: From cyclic growth to flat films. <i>Physical Review B</i> , 2016 , 94,	3.3	14
84	Ab initio study of the diffusion and decomposition pathways of SiH _x species on Si(100). <i>Physical Review B</i> , 2009 , 79,	3.3	14
83	Dynamics of pit filling in heteroepitaxy via phase-field simulations. <i>Physical Review B</i> , 2016 , 94,	3.3	14
82	Continuum modelling of semiconductor heteroepitaxy: an applied perspective. <i>Advances in Physics: X</i> , 2016 , 1, 331-367	5.1	13
81	Onset of vertical threading dislocations in Si _{1-x} Ge _x /Si (001) at a critical Ge concentration. <i>APL Materials</i> , 2013 , 1, 052109	5.7	13
80	An MD study of adatom self-diffusion on Au(110) surfaces. <i>Surface Science</i> , 1999 , 433-435, 445-448	1.8	13

79	Straining Ge bulk and nanomembranes for optoelectronic applications: a systematic numerical analysis. <i>Semiconductor Science and Technology</i> , 2014 , 29, 095012	1.8	13
78	Dislocation-Free SiGe/Si Heterostructures. <i>Crystals</i> , 2018 , 8, 257	2.3	13
77	Kinetic Control of Morphology and Composition in Ge/GeSn Core/Shell Nanowires. <i>ACS Nano</i> , 2020 , 14, 2445-2455	16.7	12
76	Hydrostatic strain enhancement in laterally confined SiGe nanostripes. <i>Physical Review B</i> , 2013 , 88,	3.3	12
75	Optimal Growth Conditions for Selective Ge Islands Positioning on Pit-Patterned Si(001). <i>Nanoscale Research Letters</i> , 2010 , 5, 1873-7	5	12
74	Understanding the elastic relaxation mechanisms of strain in Ge islands on pit-patterned Si(001) substrates. <i>Journal of Physics Condensed Matter</i> , 2008 , 20, 454217	1.8	12
73	Accelerated Molecular Dynamics Methods 2005 , 629-648		12
72	Diffusion and stability of small vacancy clusters on Cu(100) μ simulation study. <i>Surface Science</i> , 2004 , 565, 289-299	1.8	12
71	Temperature-controlled coalescence during the growth of Ge crystals on deeply patterned Si substrates. <i>Journal of Crystal Growth</i> , 2016 , 440, 86-95	1.6	11
70	Onset of plastic relaxation in the growth of Ge on Si(001) at low temperatures: Atomic-scale microscopy and dislocation modeling. <i>Physical Review B</i> , 2013 , 88,	3.3	11
69	Misfit dislocation gettering by substrate pit-patterning in SiGe films on Si(001). <i>Applied Physics Letters</i> , 2012 , 101, 013119	3.4	11
68	Multiscale modeling of island nucleation and growth during Cu(100) homoepitaxy. <i>Physical Review B</i> , 2006 , 73,	3.3	10
67	Reduction of threading dislocation density beyond the saturation limit by optimized reverse grading. <i>Physical Review Materials</i> , 2020 , 4,	3.2	10
66	Detailed Analysis of the Shape-dependent Deformation Field in 3D Ge Islands 2008 , 421-438		10
65	The origin and nature of killer defects in 3C-SiC for power electronic applications by a multiscale atomistic approach. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 8380-8392	7.1	9
64	Dislocation engineering in SiGe heteroepitaxial films on patterned Si (001) substrates. <i>Applied Physics Letters</i> , 2011 , 98, 121908	3.4	9
63	A fast computational method for determining equilibrium concentration profiles in intermixed nanoislands. <i>Journal of Physics Condensed Matter</i> , 2009 , 21, 084217	1.8	9
62	Assessing the composition of hetero-epitaxial islands via morphological analysis: an analytical model matching GeSi/Si(001) data. <i>Journal of Physics Condensed Matter</i> , 2012 , 24, 104018	1.8	9

61	Ab-initio adiabatic noble gas-metal interaction: the role of the induced polarization charge. <i>Surface Science</i> , 1998 , 401, L383-L387	1.8	9
60	Long-jump probabilities in a BGK model for surface diffusion. <i>Chemical Physics Letters</i> , 1999 , 315, 153-157	5	9
59	Reduced-Pressure Chemical Vapor Deposition Growth of Isolated Ge Crystals and Suspended Layers on Micrometric Si Pillars. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 26374-26380	9.5	9
58	Strain and strain-release engineering at epitaxial SiGe islands on Si(0 0 1) for microelectronic applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009 , 159-160, 90-94	3.1	8
57	A multiscale model of the plasma assisted deposition of crystalline silicon. <i>Surface and Coatings Technology</i> , 2007 , 201, 8863-8867	4.4	8
56	Atomic-scale modeling of next-layer nucleation and step flow at the Ge(105) rebonded-step surface. <i>Physical Review B</i> , 2007 , 75,	3.3	8
55	Transition-path spectra at metal surfaces. <i>Surface Science</i> , 2003 , 543, 141-152	1.8	8
54	Universal law for piecewise dimer diffusion. <i>Physical Review B</i> , 1999 , 60, 11102-11109	3.3	8
53	Molecular dynamics simulations of extended defects and their evolution in 3C-SiC by different potentials. <i>Modelling and Simulation in Materials Science and Engineering</i> , 2020 , 28, 015002	2	8
52	From plastic to elastic stress relaxation in highly mismatched SiGe/Si heterostructures. <i>Acta Materialia</i> , 2016 , 114, 97-105	8.4	7
51	Strain Engineering in Highly Mismatched SiGe/Si Heterostructures. <i>Materials Science in Semiconductor Processing</i> , 2017 , 70, 117-122	4.3	7
50	Binding sites for SiH ₂ /Si(0 0 1): A combined ab initio, tight-binding, and classical investigation. <i>Surface Science</i> , 2006 , 600, 4445-4453	1.8	7
49	Atomistic simulation of a 60° shuffle dislocation segment migrating in a Ge/SiGe(001) epitaxial film. <i>Journal of Physics Condensed Matter</i> , 2005 , 17, 7505-7515	1.8	7
48	Mobility of atomic chains on channeled surfaces. <i>Journal of Chemical Physics</i> , 2000 , 113, 349-356	3.9	7
47	Structure and Stability of Partial Dislocation Complexes in 3C-SiC by Molecular Dynamics Simulations. <i>Materials</i> , 2019 , 12,	3.5	6
46	Dynamics of crosshatch patterns in heteroepitaxy. <i>Physical Review B</i> , 2019 , 100,	3.3	6
45	Si/Ge exchange mechanisms at the Ge(105) surface. <i>Physical Review B</i> , 2010 , 81,	3.3	6
44	Impact-driven effects in thin-film growth: steering and transient mobility at the Ag(110) surface. <i>Nanotechnology</i> , 2006 , 17, 3556-62	3.4	6

43	Relaxed SiGe heteroepitaxy on Si with very thin buffer layers: experimental LEPECVD indications and an interpretation based on strain-dependent dislocation nature. <i>Microelectronic Engineering</i> , 2004 , 76, 290-296	2.5	6
42	Misfit-Dislocation Distributions in Heteroepitaxy: From Mesoscale Measurements to Individual Defects and Back. <i>Physical Review Applied</i> , 2018 , 10,	4.3	6
41	Growth and Coalescence of 3C-SiC on Si(111) Micro-Pillars by a Phase-Field Approach. <i>Materials</i> , 2019 , 12,	3.5	5
40	A self-ordered, body-centered tetragonal superlattice of SiGe nanodot growth by reduced pressure CVD. <i>Nanotechnology</i> , 2017 , 28, 485303	3.4	5
39	Self-Ordering of Misfit Dislocation Segments in Epitaxial SiGe Islands on Si(001). <i>Journal of Applied Physics</i> , 2011 , 110, 044310	2.5	5
38	Diffusion of one-dimensional clusters on Au and Pt(110) (1 $\bar{1}$). <i>Surface Science</i> , 2000 , 454-456, 575-578	1.8	5
37	Sunburst pattern by kinetic segregation in core-shell nanowires: A phase-field study. <i>Applied Surface Science</i> , 2020 , 517, 146056	6.7	4
36	Selective Area Epitaxy of GaAs/Ge/Si Nanomembranes: A Morphological Study. <i>Crystals</i> , 2020 , 10, 57	2.3	4
35	Structure, interface abruptness and strain relaxation in self-assisted grown InAs/GaAs nanowires. <i>Applied Surface Science</i> , 2017 , 395, 29-36	6.7	4
34	Interaction of SiH _x precursors with hydrogen-covered Si surfaces: Impact dynamics and adsorption sites. <i>Surface Science</i> , 2007 , 601, 3970-3973	1.8	4
33	Leapfrog-induced selective faceting in the growth of missing-row (110) surfaces. <i>Chemical Physics Letters</i> , 2004 , 398, 50-55	2.5	4
32	Probability of dimer reassociation in two dimensions. <i>Physical Review E</i> , 2000 , 61, 3411-6	2.4	4
31	Three-dimensional SiGe/Si heterostructures: Switching the dislocation sign by substrate under-etching. <i>Physical Review Materials</i> , 2017 , 1,	3.2	4
30	Controlling the relaxation mechanism of low strain Si _{1-x} Gex/Si(001) layers and reducing the threading dislocation density by providing a preexisting dislocation source. <i>Journal of Applied Physics</i> , 2020 , 128, 215305	2.5	4
29	Modeling the evolution of germanium islands on silicon(001) thin films 2011 , 211-246		3
28	Theoretical evidence for fast H-divacancy rotation on H/Pd(111). <i>Chemical Physics Letters</i> , 2004 , 400, 163-168	2.5	3
27	Computational Analysis of Low-Energy Dislocation Configurations in Graded Layers. <i>Crystals</i> , 2020 , 10, 661	2.3	3
26	Enhancing elastic stress relaxation in SiGe/Si heterostructures by Si pillar necking. <i>Applied Physics Letters</i> , 2016 , 109, 182112	3.4	3

25	Self-Assembly of Nanovoids in Si Microcrystals Epitaxially Grown on Deeply Patterned Substrates. <i>Crystal Growth and Design</i> , 2020 , 20, 2914-2920	3.5	2
24	Unexpected Dominance of Vertical Dislocations in High-Misfit Ge/Si(001) Films and Their Elimination by Deep Substrate Patterning (Adv. Mater. 32/2013). <i>Advanced Materials</i> , 2013 , 25, 4407-4407	2.4	2
23	Strained MOSFETs on ordered SiGe dots. <i>Solid-State Electronics</i> , 2011 , 65-66, 81-87	1.7	2
22	Atomistic approach for Boron Transient Enhanced Diffusion and clustering 2008 ,		2
21	Charge transfer in chemisorption: N and Si on Al. <i>Solid State Communications</i> , 1996 , 99, 7-11	1.6	2
20	Thermodynamic driving force in the formation of hexagonal-diamond Si and Ge nanowires. <i>Applied Surface Science</i> , 2021 , 545, 148948	6.7	2
19	Atomic-scale insights on the formation of ordered arrays of edge dislocations in Ge/Si(001) films via molecular dynamics simulations.. <i>Scientific Reports</i> , 2022 , 12, 3235	4.9	2
18	Fully coherent Ge islands growth on Si nano-pillars by selective epitaxy. <i>Materials Science in Semiconductor Processing</i> , 2017 , 70, 30-37	4.3	1
17	Delayed plastic relaxation limit in SiGe islands grown by Ge diffusion from a local source. <i>Journal of Applied Physics</i> , 2015 , 117, 104309	2.5	1
16	Elastic and Plastic Stress Relaxation in Highly Mismatched SiGe/Si Crystals. <i>MRS Advances</i> , 2016 , 1, 3403-3408	3.08	1
15	Density functional study of the decomposition pathways of SiH ₄ and GeH ₄ at the Si(100) and Ge(100) surfaces. <i>Journal of Physics Condensed Matter</i> , 2012 , 24, 104002	1.8	1
14	Reentrant Behavior of the Density vs. Temperature of Indium Islands on GaAs(111)A. <i>Nanomaterials</i> , 2020 , 10,	5.4	1
13	Anisotropic extended misfit dislocations in overcritical SiGe films by local substrate patterning. <i>Nanotechnology</i> , 2016 , 27, 425301	3.4	1
12	Motion of crystalline inclusions by interface diffusion in the proximity of free surfaces. <i>Journal of Nanoparticle Research</i> , 2019 , 21, 1	2.3	1
11	Alignment control of self-ordered three dimensional SiGe nanodots. <i>Semiconductor Science and Technology</i> , 2018 , 33, 114014	1.8	1
10	Faceting of Si and Ge crystals grown on deeply patterned Si substrates in the kinetic regime: phase-field modelling and experiments. <i>Scientific Reports</i> , 2021 , 11, 18825	4.9	1
9	Stress-Induced Acceleration and Ordering in Solid-State Dewetting.. <i>Physical Review Letters</i> , 2022 , 128, 026101	7.4	0
8	Nature and Shape of Stacking Faults in 3C-SiC by Molecular Dynamics Simulations. <i>Physica Status Solidi (B): Basic Research</i> , 2021 , 258, 2000598	1.3	0

- 7 Machine learning potential for interacting dislocations in the presence of free surfaces.. *Scientific Reports*, **2022**, 12, 3760 4.9 ○
- 6 Phenomenological model of nanocrystalline silicon film formation by plasma-enhanced chemical vapor deposition. *Optoelectronics, Instrumentation and Data Processing*, **2009**, 45, 322-327 0.6
- 5 Spontaneous Ge island ordering promoted by partial silicon capping. *Materials Science in Semiconductor Processing*, **2006**, 9, 823-827 4.3
- 4 Comment on Scaling behavior of one-dimensional Pt chains migration on Pt(110)-(1 \times 1) surface \square *Physics Letters, Section A: General, Atomic and Solid State Physics*, **2000**, 277, 185-187 2.3
- 3 Diffusion of Adatoms and Small Clusters on Missing-Row-Reconstructed Surfaces. *NATO Science Series Series II, Mathematics, Physics and Chemistry*, **2001**, 237-245
- 2 Slip trace-induced terrace erosion. *Applied Surface Science*, **2019**, 466, 454-458 6.7
- 1 Prismatic Ge-rich inclusions in the hexagonal SiGe shell of GaP-Si-SiGe nanowires by controlled faceting. *Nanoscale*, **2021**, 13, 9436-9445 7.7